

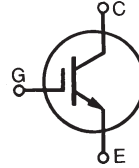
# IGBT

Optimized for  
switching up to 5KHz

**IXGA 12N120A2**  
**IXGP 12N120A2**

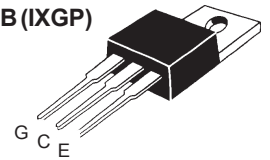
$V_{CES} = 1200\text{ V}$   
 $I_{C25} = 24\text{ A}$   
 $V_{CE(sat)} = 3.0\text{ V}$

Preliminary data sheet

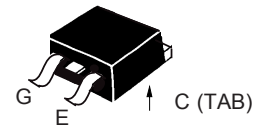


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	24	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	12	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1\text{ ms}$	48	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15\text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 100\ \Omega$ Clamped inductive load	$I_{CM} = 24$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	75	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 0.55/5	Nm/lb.in.
<b>Weight</b>	TO-220	4	g
	TO-263	2	g

TO-220AB (IXGP)



TO-263 AA (IXGA)



## Features

- International standard packages  
JEDEC TO-220AB and TO-263AA
- Low  $V_{CE(sat)}$   
- for minimum on-state conduction losses
- MOS Gate turn-on  
- drive simplicity

## Applications

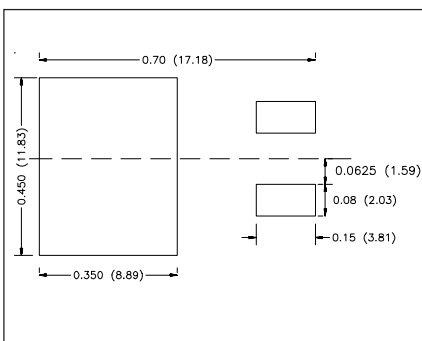
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge

## Advantages

- Easy to mount with one screw
- Reduces assembly time and cost
- High power density

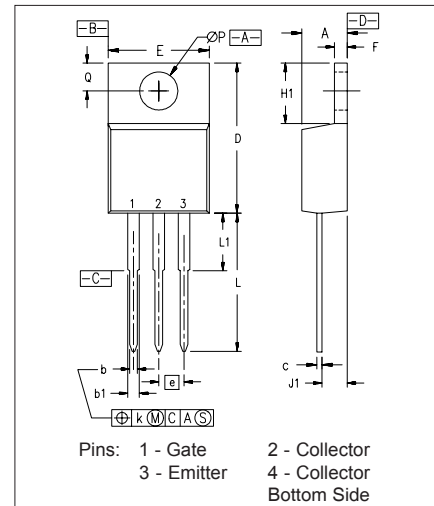
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\ \mu\text{A}, V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = V_{CES}$ $V_{GE} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		25 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		250 $\mu\text{A}$
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15\text{ V}$	2.4	3.0	V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values			
		Min.	Typ.	Max.	
$g_{fs}$	$I_C = I_{C90}$ , $V_{CE} = 10\text{ V}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	4.0	7.8	S	
$I_{C(on)}$	$V_{GE} = 10\text{ V}$ , $V_{CE} = 10\text{ V}$		35	A	
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		530	pF	
$C_{oes}$			30	pF	
$C_{res}$			4	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		24	nC	
$Q_{ge}$			5.5	nC	
$Q_{gc}$			8.8	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ $V_{CE} = 960\text{ V}$ , $R_G = R_{off} = 100\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 V_{CES}$ , higher $T_J$ or increased $R_G$		15	ns	
$t_{ri}$			30	ns	
$t_{d(off)}$			680	1000	ns
$t_{fi}$			650	1000	ns
$E_{off}$			5.4	9.0	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ $V_{CE} = 960\text{ V}$ , $R_G = R_{off} = 100\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 V_{CES}$ , higher $T_J$ or increased $R_G$		15	ns	
$t_{ri}$			30	ns	
$E_{on}$			0.5	mJ	
$t_{d(off)}$			700	ns	
$E_{off}$			1050	ns	
$R_{thJC}$	TO-220		1.66	K/W	
$R_{thCK}$			0.5	K/W	



**Min. Recommended Footprint**  
(Dimensions in inches and mm)

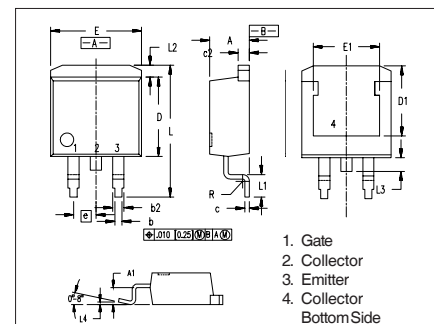
### TO-220 AB Dimensions



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

### TO-263 AA Outline

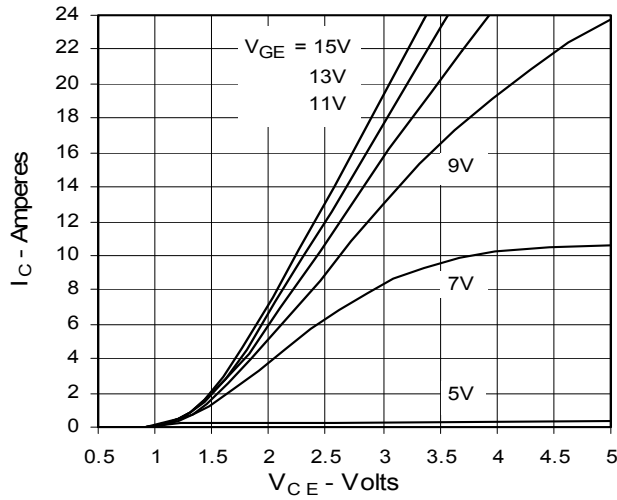


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

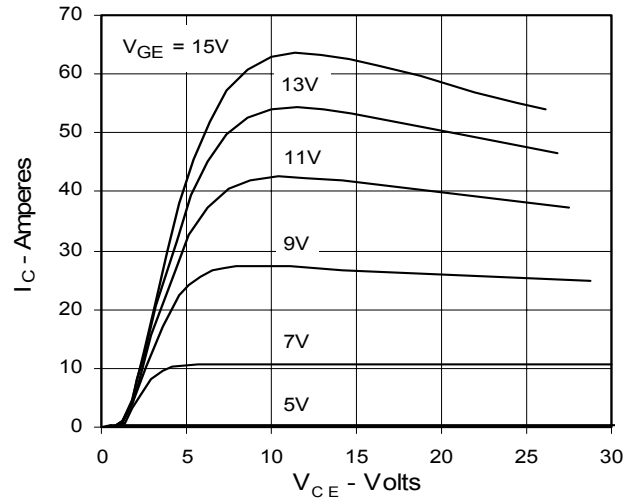
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

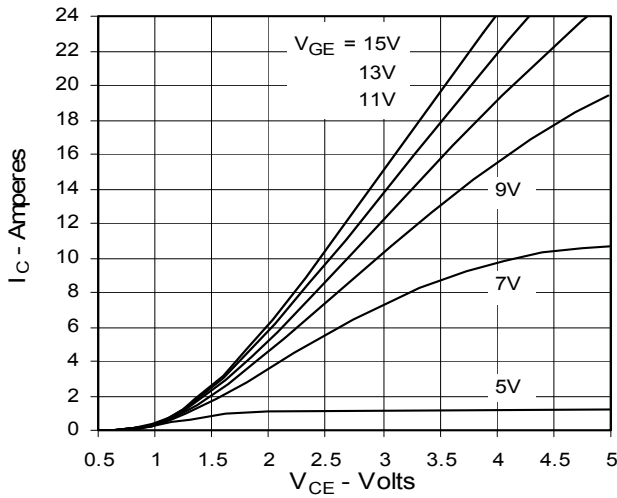
**Fig. 1. Output Characteristics**  
@ 25 °C



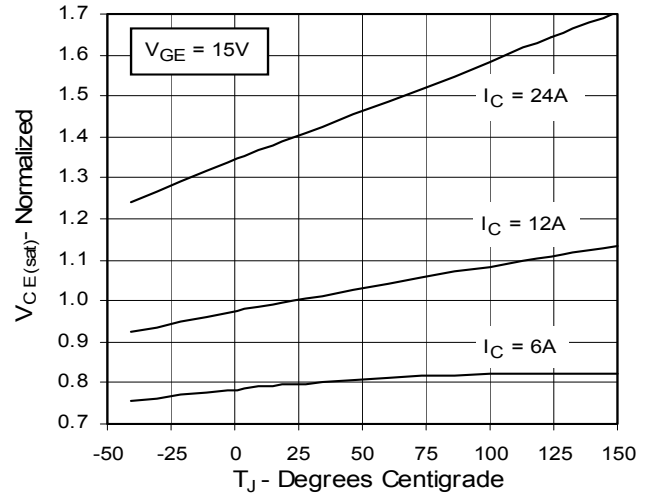
**Fig. 2. Extended Output Characteristics**  
@ 25 °C



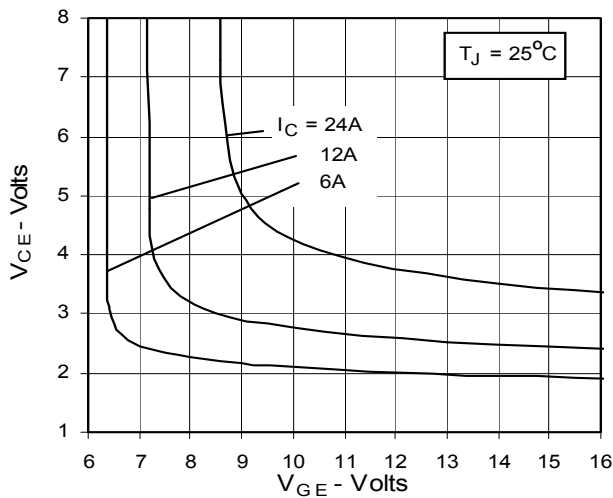
**Fig. 3. Output Characteristics**  
@ 125 °C



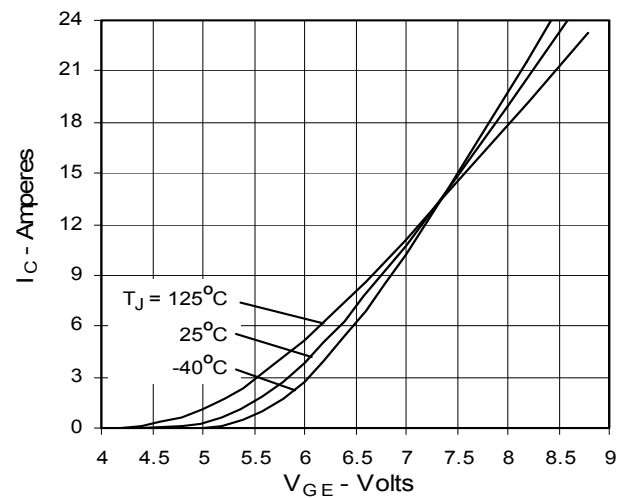
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Temperature**



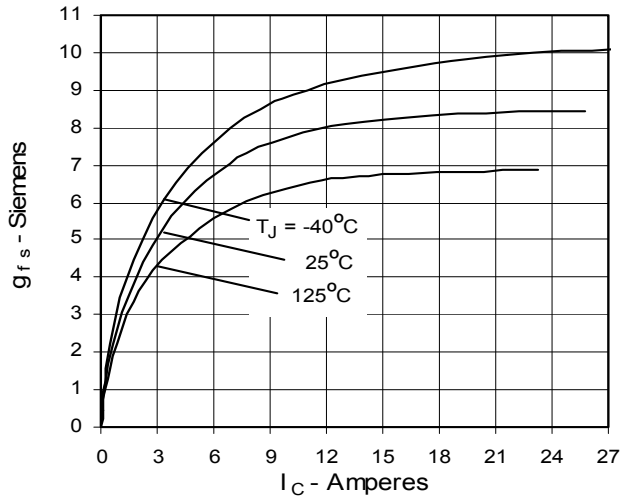
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage**



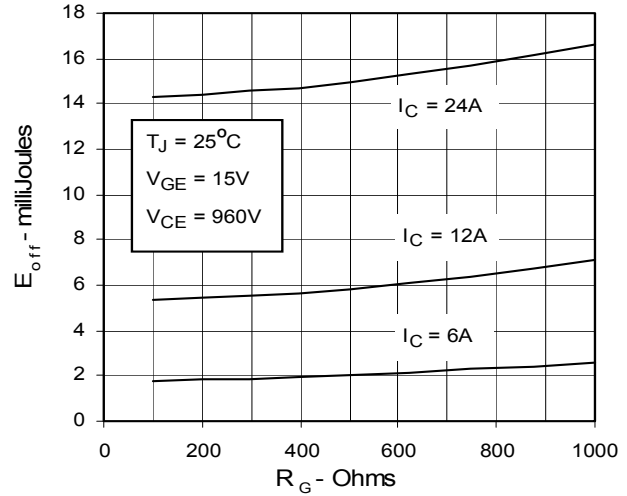
**Fig. 6. Input Admittance**



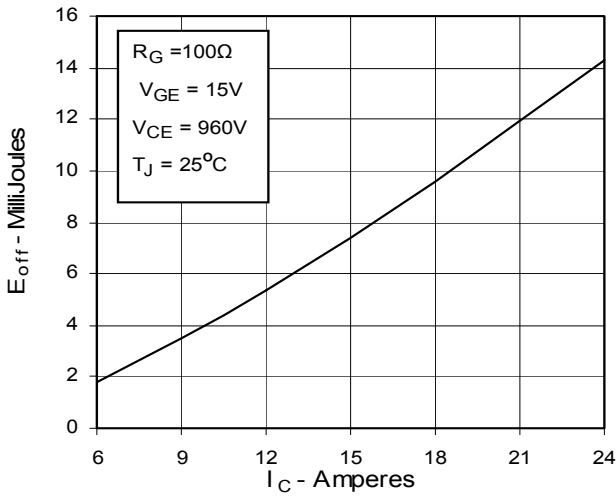
**Fig. 7. Transconductance**



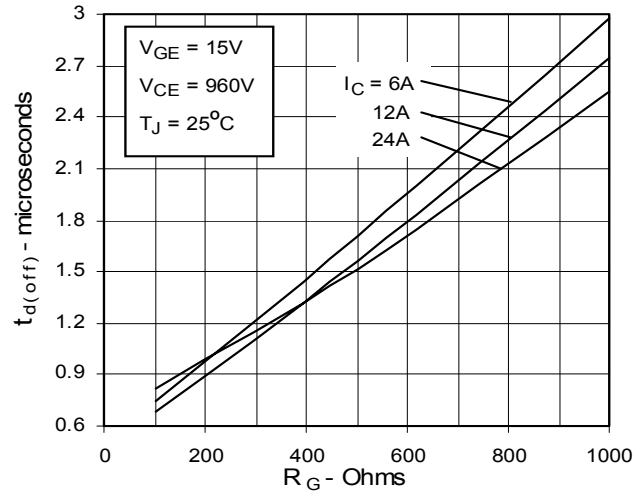
**Fig. 8. Dependence of Turn-off Energy Loss on  $R_G$**



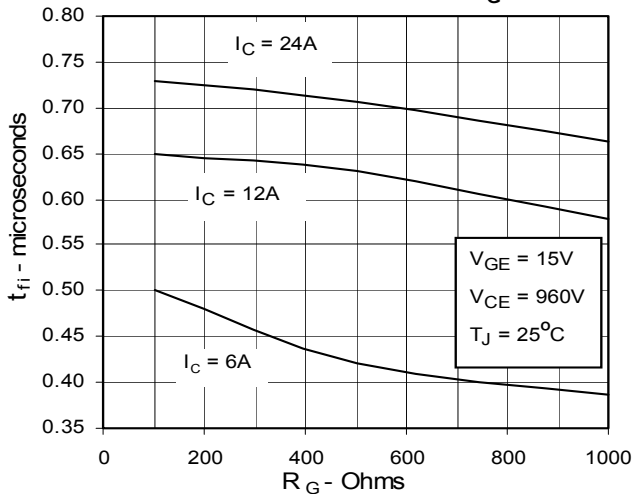
**Fig. 9. Dependence of Turn-Off Energy Loss on  $I_C$**



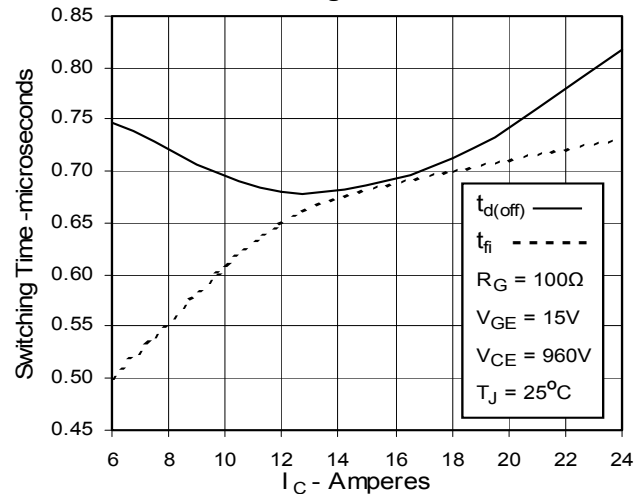
**Fig. 10. Dependence of Turn-off Delay Time on  $R_G$**



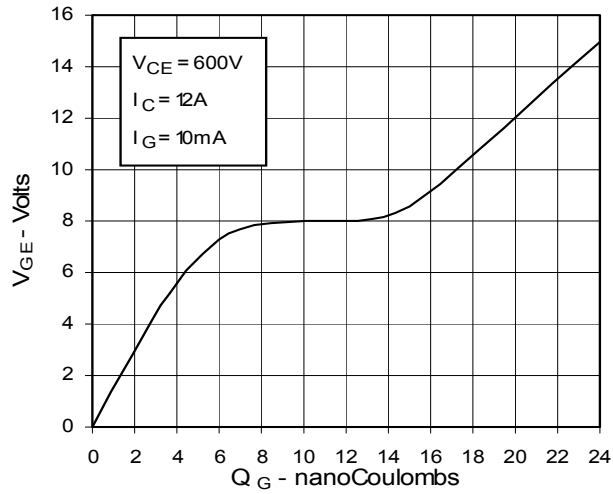
**Fig. 11. Dependence of Turn-off Current Fall Time on  $R_G$**



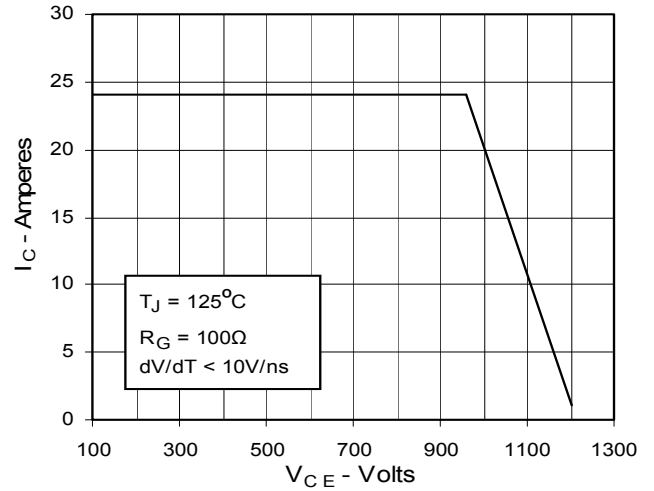
**Fig. 12. Dependence of Turn-off Switching Time on  $I_C$**



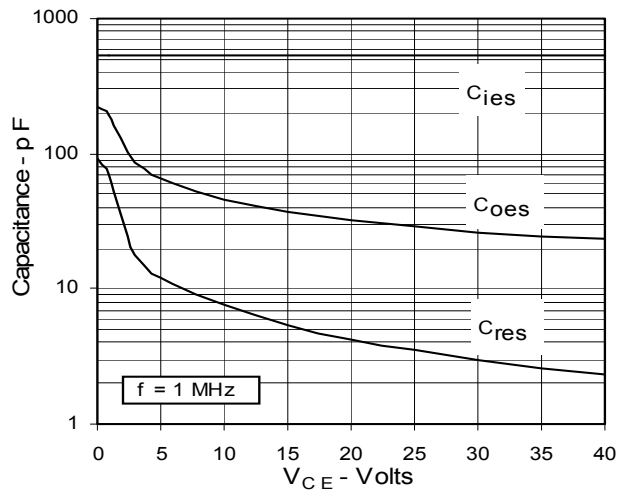
**Fig. 13. Gate Charge**



**Fig. 14. Reverse-Bias Safe Operating Area**



**Fig. 15. Capacitance**



**Fig. 17. Maximum Transient Thermal Resistance**

